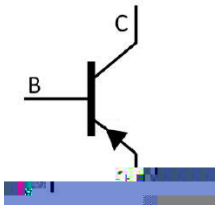
Silicon PNP transistor in a TO-92 Plastic Package.

Complementary pair with 2SC1213(A).

Low frequency power amplifier.





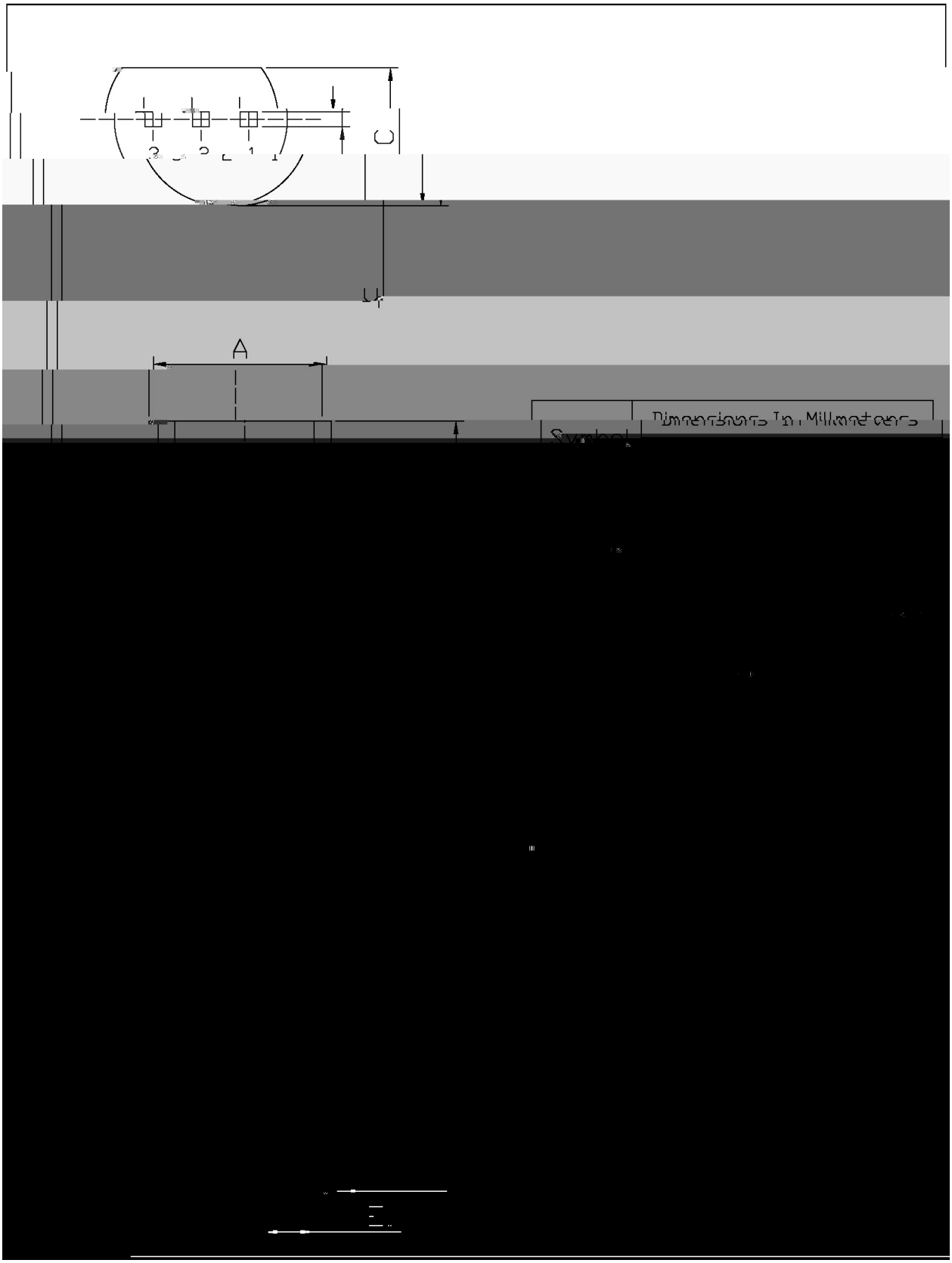
PIN1 Base PIN 2 Collector PIN 3 Emitter

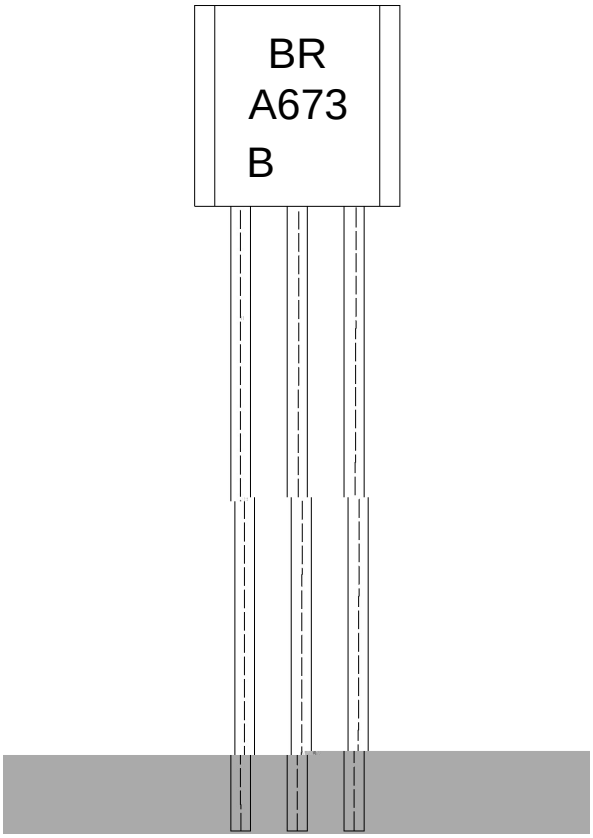
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SA673	-35	V
		2SA673A	-50	
Collector to Emitter Voltage	V_{CEO}	2SA673	-35	V
		2SA673A	-50	
Emitter to Base Voltage	V_{EBO}		-4.0	V
Collector Current - Continuous	I_C		-500	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	2SA673	I_C=-10 A I_E=0	-35			V
		2SA673A		-50			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SA673	I_C=-1.0mA I_B=0	-35			V
		2SA673A		-50			
Emitter to Base Breakdown Voltage	V_{EBO}		I_E=-10 A I_C=0	-4.0			V
Collector Cut-Off Current	I_{CBO}		V_{CB}=-20V I_E=0			-0.5	A
DC Current Gain	$h_{FE(1)}$		V_{CE}=-3.0V I_C=-10mA	60		320	
	$h_{FE(2)}$		V_{CE}=-3.0V I_C=-500mA	10			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		I_C=-150mA I_B=-15mA		-0.2	-0.6	V
Base to Emitter Voltage	V_{BE}		V_{CE}=-3.0V I_C=-10mA		-0.64		V



TO-92 Unit: mm

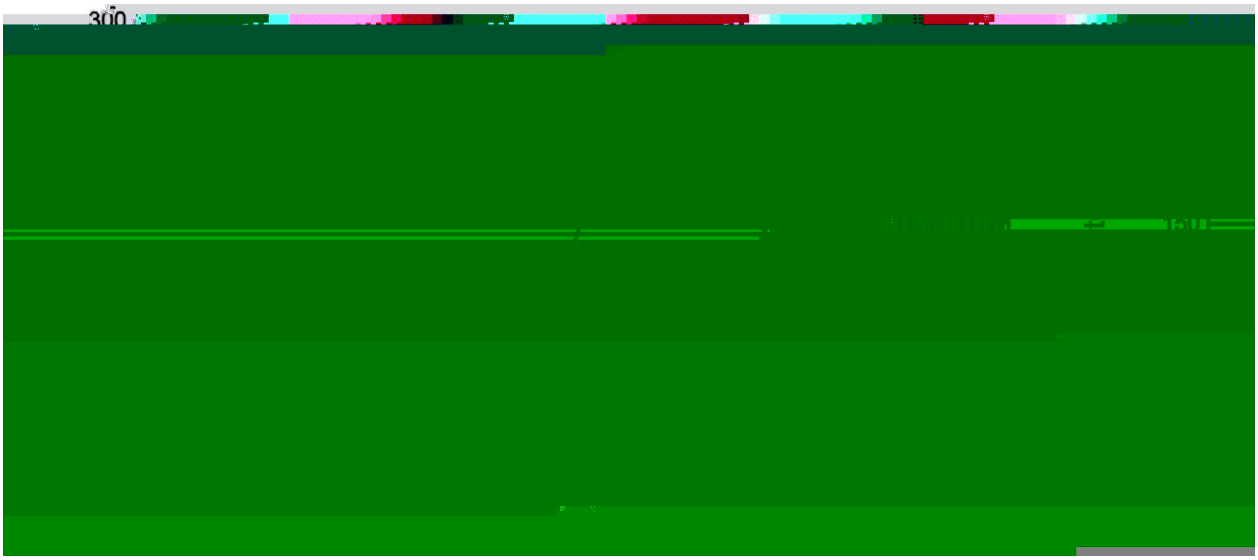




h_{FE}

Note:

BR:	Company Code.
A673:	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec. Temp:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱